

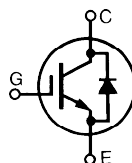
XPT™ 650V IGBT

IXXX140N65B4H1

GenX4™

w/Sonic Diode

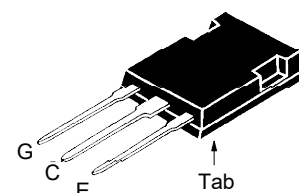
Extreme Light Punch Through
IGBT for 10-30kHz Switching



$$\begin{aligned} V_{CES} &= 650V \\ I_{C110} &= 140A \\ V_{CE(sat)} &\leq 1.90V \\ t_{fi(typ)} &= 44ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 175°C	650	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 175°C , $R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	340	A
I_{LRMS}	Terminal Current Limit	160	A
I_{C110}	$T_C = 110^\circ\text{C}$	140	A
I_{F110}	$T_C = 110^\circ\text{C}$	72	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	840	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ\text{C}$, $R_G = 4.7\Omega$ Clamped Inductive Load	$I_{CM} = 240$ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 400V$, $T_J = 150^\circ\text{C}$ $R_G = 10\Omega$, Non Repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	1200	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
F_C	Mounting Force	20..120 / 4.5..27	N/lb
Weight		6	g

PLUS247



G = Gate E = Emitter
C = Collector Tab = Collector

Features

- Optimized for 10-30kHz Switching
- Square RBSOA
- Short Circuit Capability
- Anti-Parallel Sonic Diode
- High Current Handling Capability
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- High Frequency Power Inverters

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ\text{C}$			25 μA 5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 120A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$	1.55 1.76		V V

Symbol Test Conditions $(T_J = 25^\circ\text{C}$ Unless Otherwise Specified)**Characteristic Values****Min.** **Typ.** **Max.**

g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}$, Note 1	40	70	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		8000	pF
C_{oes}			560	pF
C_{res}			107	pF
$Q_{g(on)}$	$I_C = 140\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		250	nC
Q_{ge}			70	nC
Q_{gc}			90	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 4.7\Omega$ Note 2		54	ns
t_{ri}			105	ns
E_{on}			5.75	mJ
$t_{d(off)}$			270	ns
t_{fi}			44	ns
E_{off}			2.67	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 4.7\Omega$ Note 2		43	ns
t_{ri}			85	ns
E_{on}			6.80	mJ
$t_{d(off)}$			240	ns
t_{fi}			100	ns
E_{off}			3.90	mJ
R_{thJC}				0.125 $^\circ\text{C/W}$
R_{thCS}			0.15	$^\circ\text{C/W}$

Reverse Sonic Diode (FRD)**Symbol Test Conditions** $(T_J = 25^\circ\text{C}$ Unless Otherwise Specified)**Characteristic Values****Min.** **Typ.** **Max.**

V_F	$I_F = 100\text{A}, V_{GE} = 0\text{V}$, Note 1	$T_J = 150^\circ\text{C}$	2.1	2.5	V
			2.2		V
I_{RM}	$I_F = 100\text{A}, V_{GE} = 0\text{V}, T_J = 150^\circ\text{C}$ $-di_F/dt = 600\text{A}/\mu\text{s}, V_R = 400\text{V}$		43		A
t_{rr}			210		ns
R_{thJC}				0.24	$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (Clamp), T_J or R_G .

Littelfuse reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

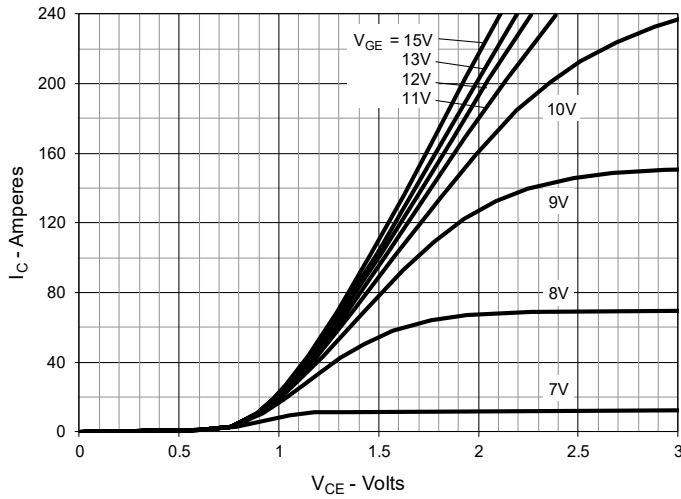


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

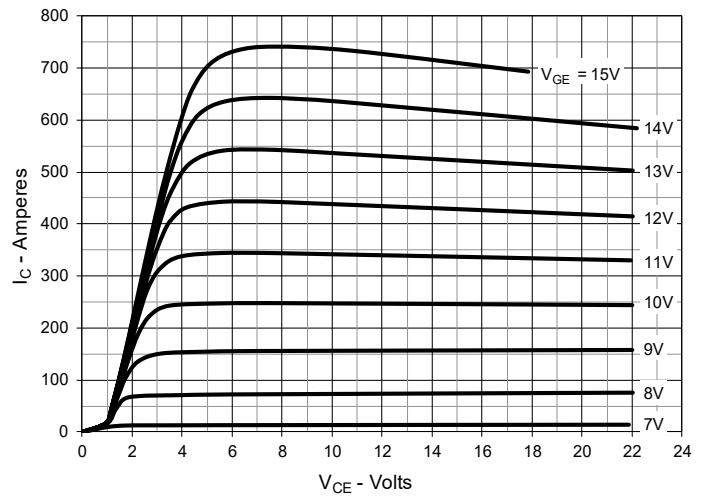


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

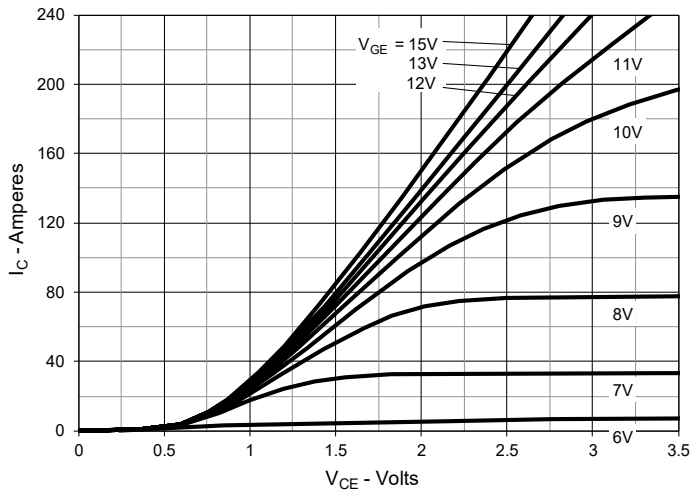


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

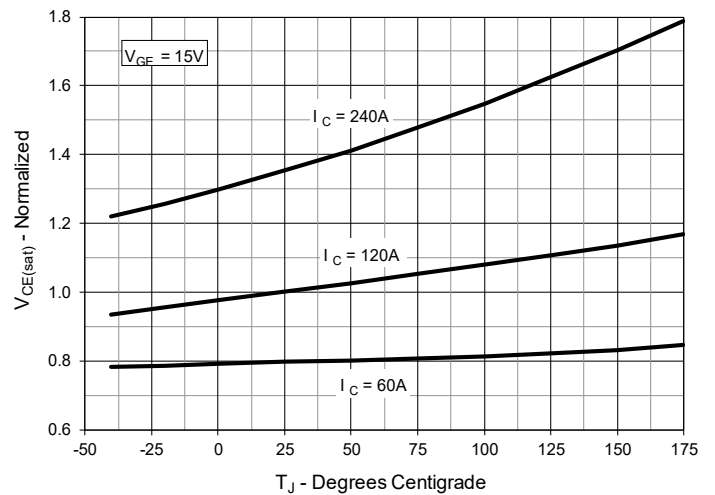


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

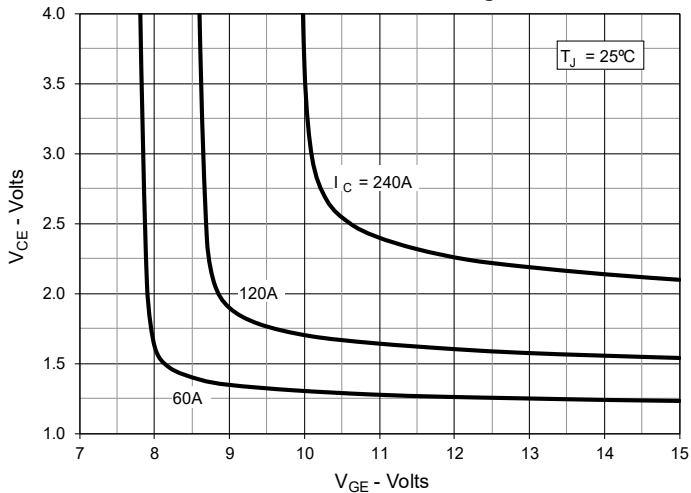


Fig. 6. Input Admittance

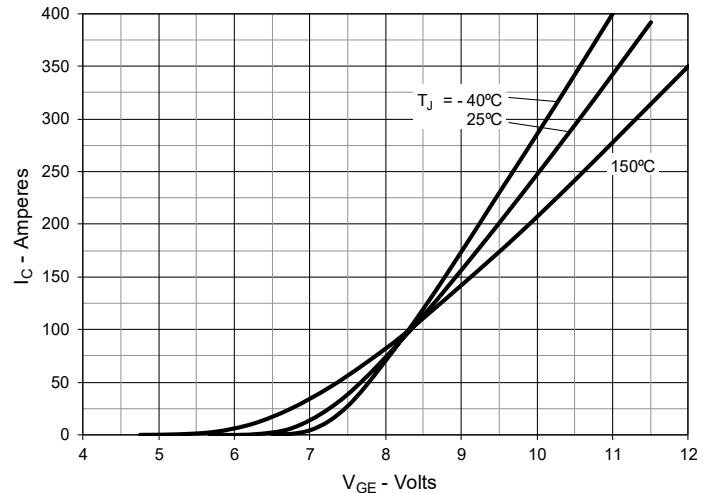


Fig. 7. Transconductance

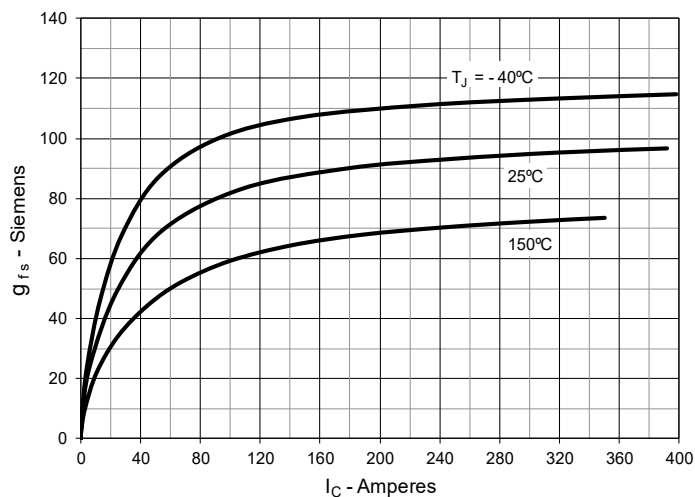


Fig. 8. Gate Charge

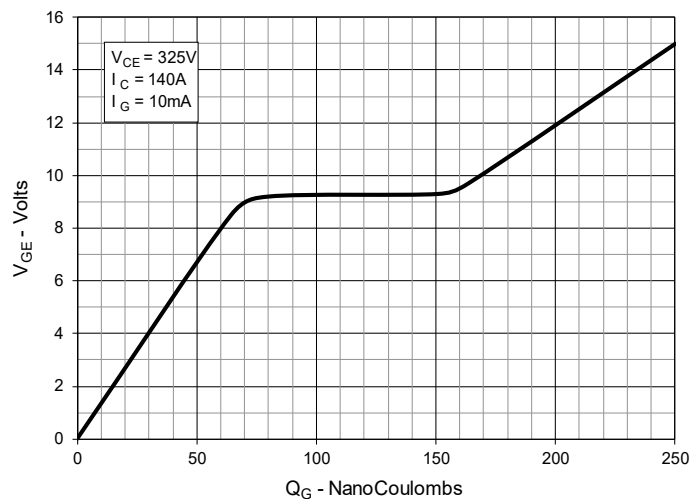


Fig. 9. Capacitance

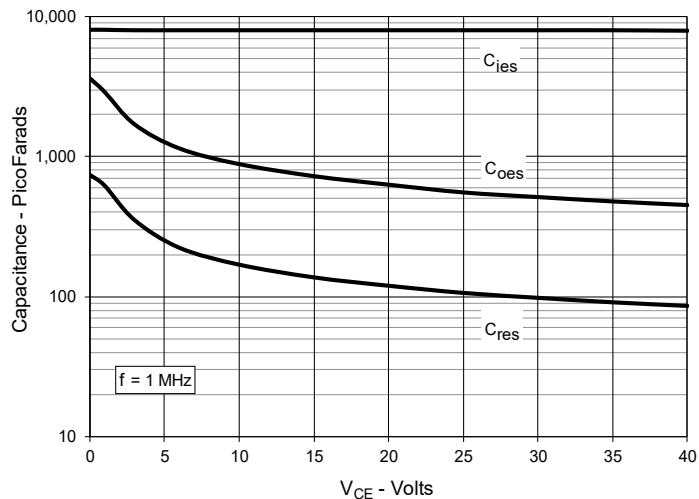


Fig. 10. Reverse-Bias Safe Operating Area

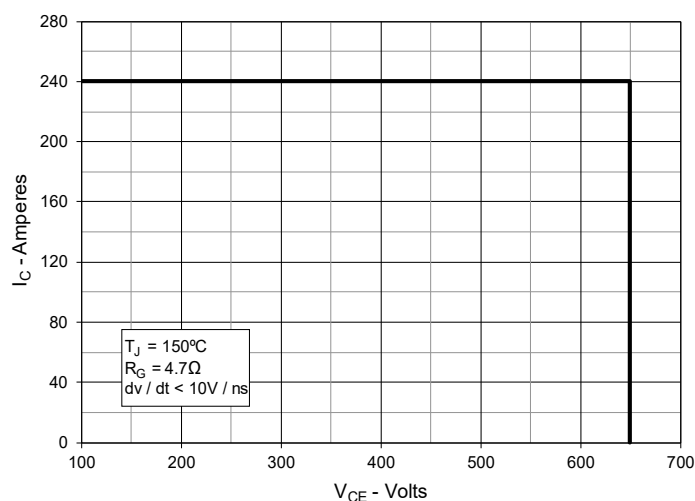


Fig. 11. Forward-Bias Safe Operating Area

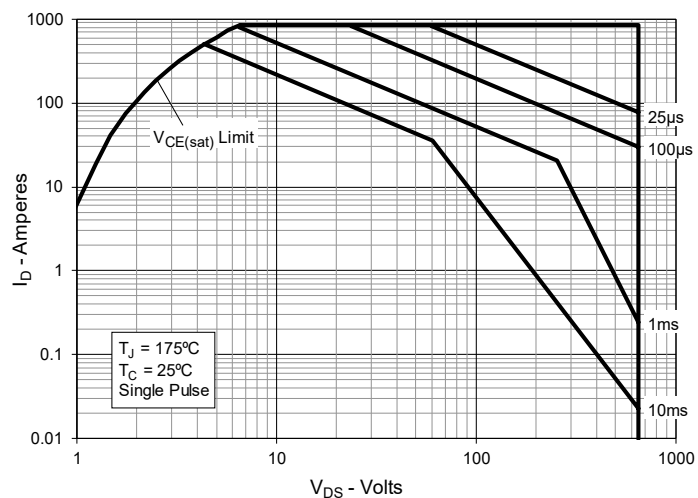


Fig. 12. Maximum Transient Thermal Impedance (IGBT)

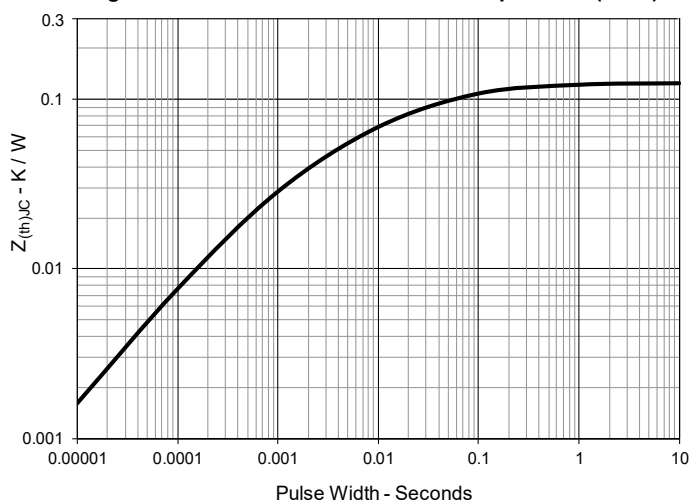


Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

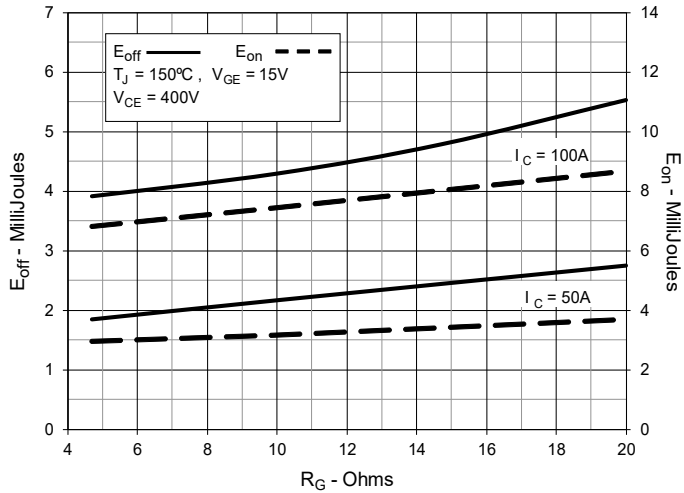


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

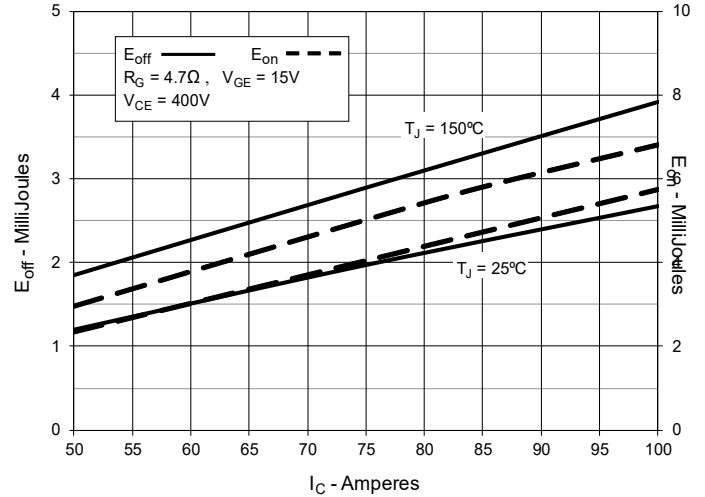


Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

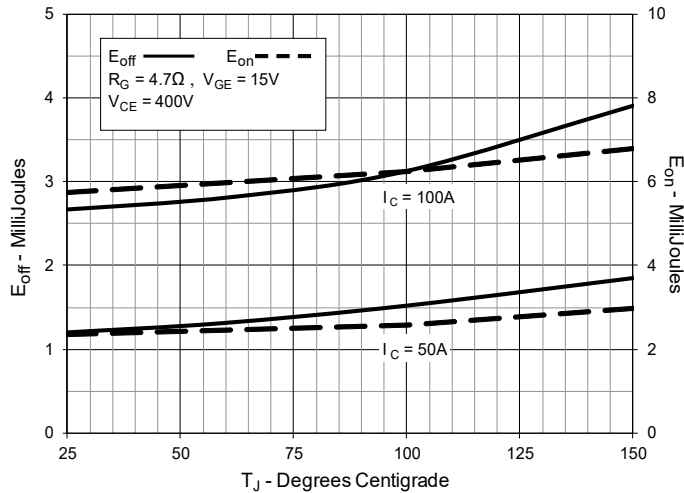


Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

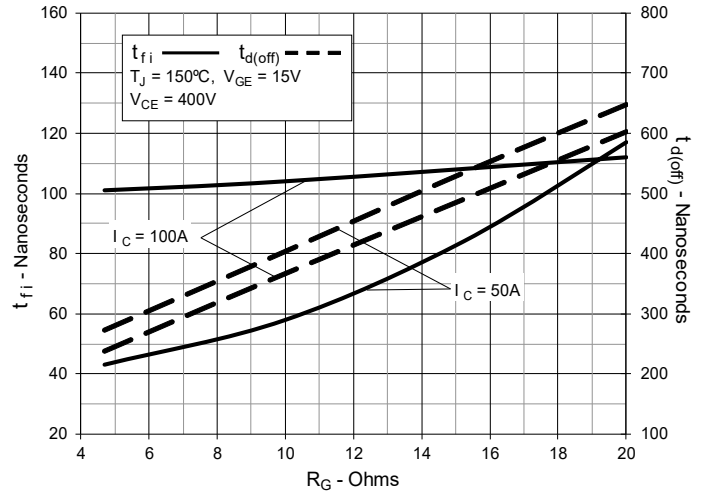


Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

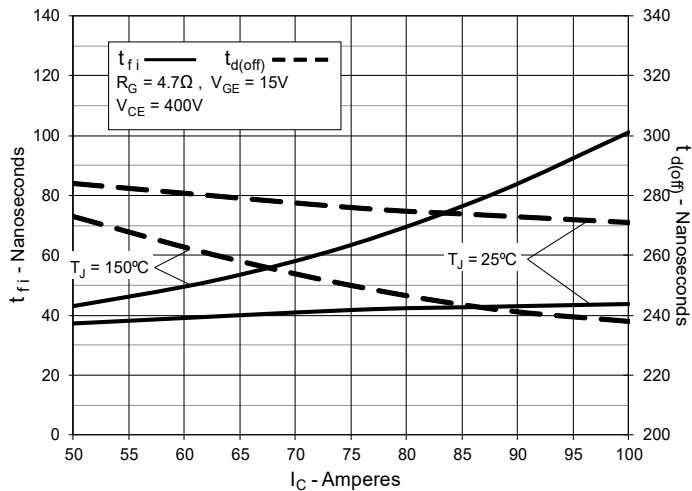


Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature

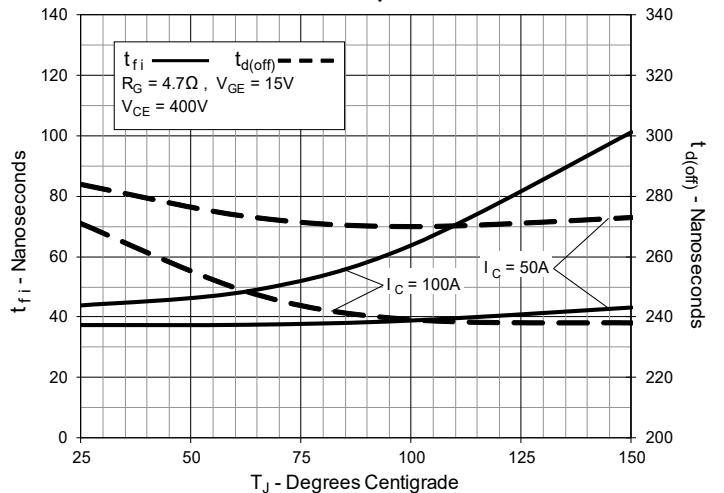


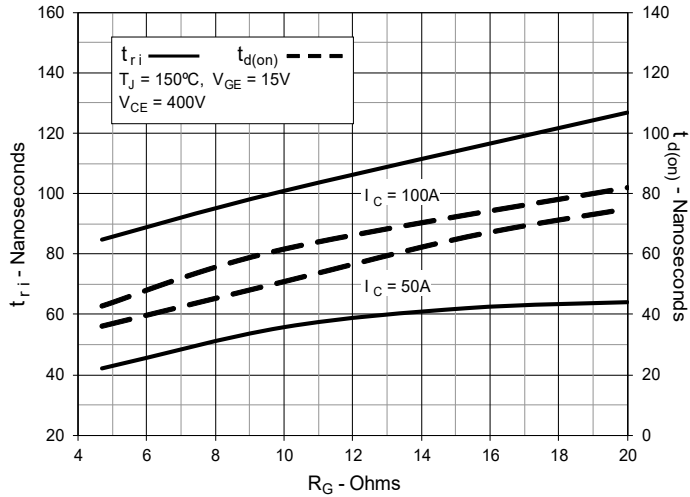
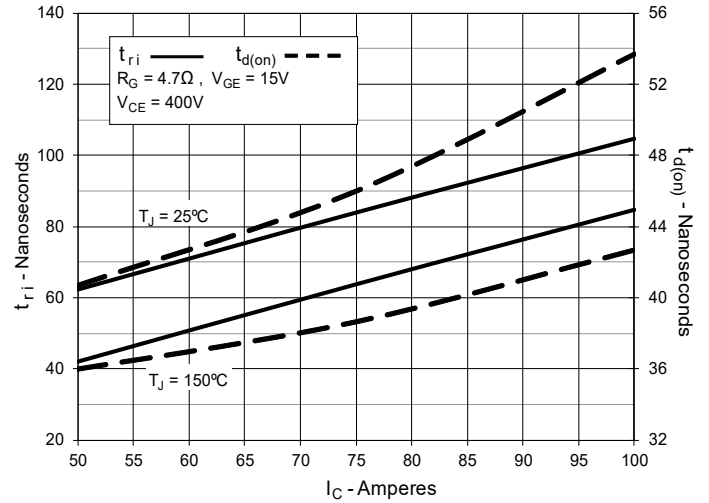
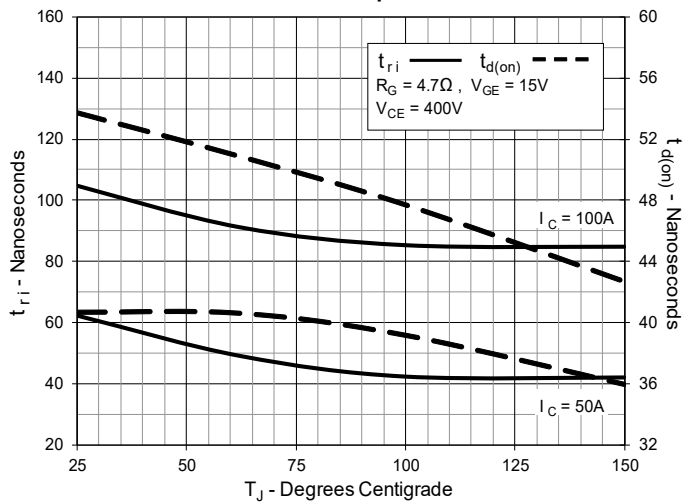
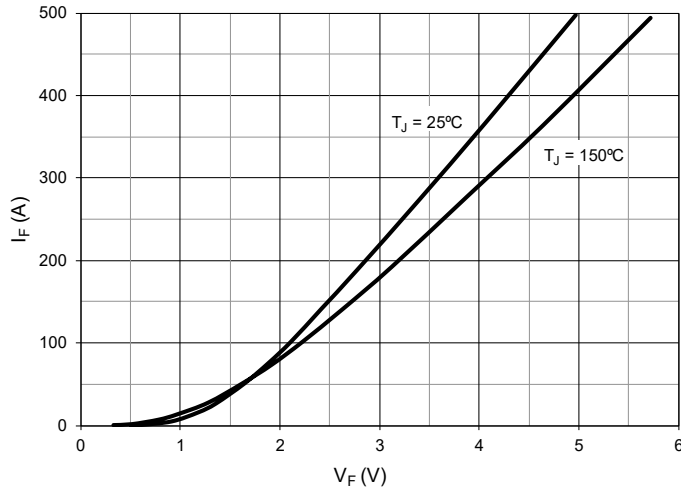
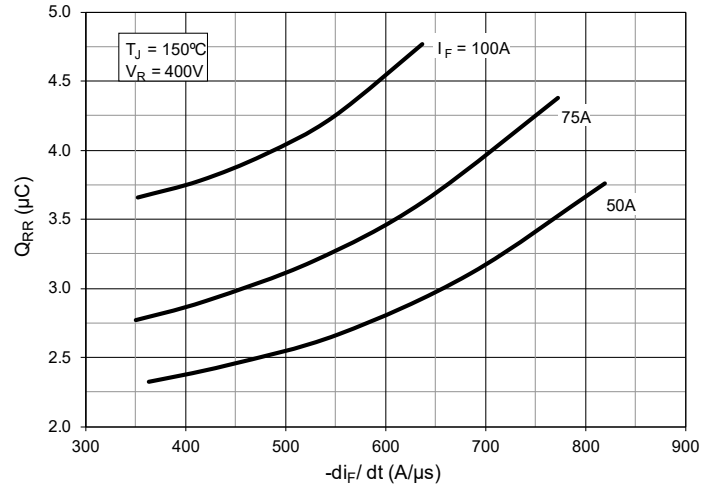
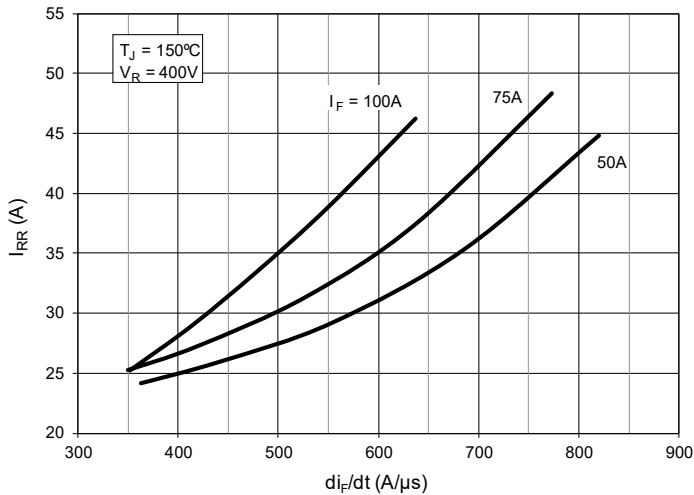
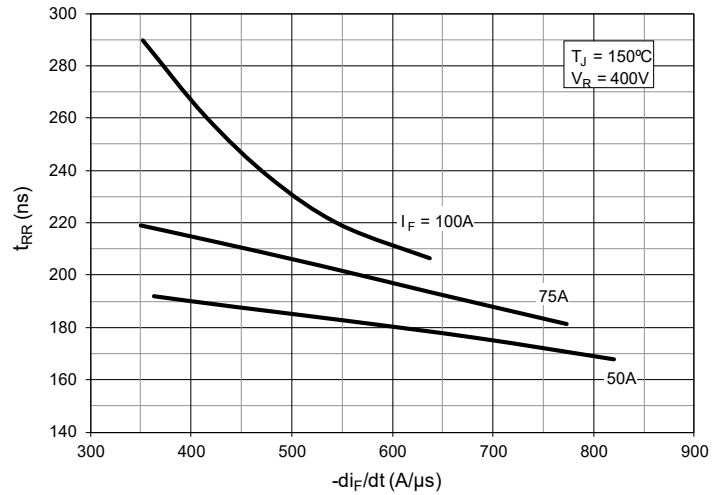
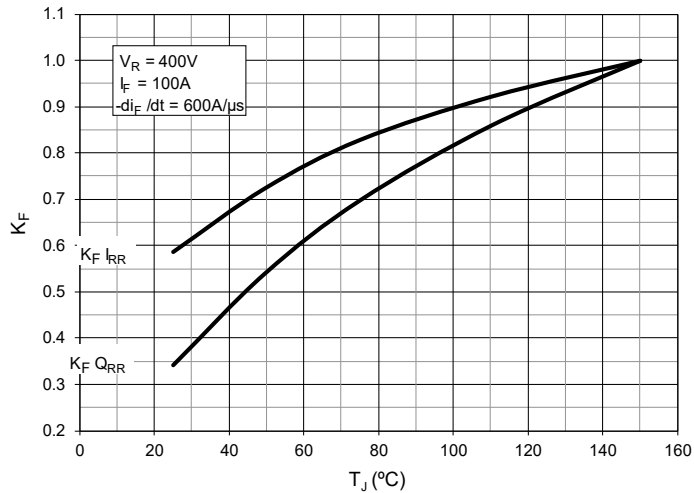
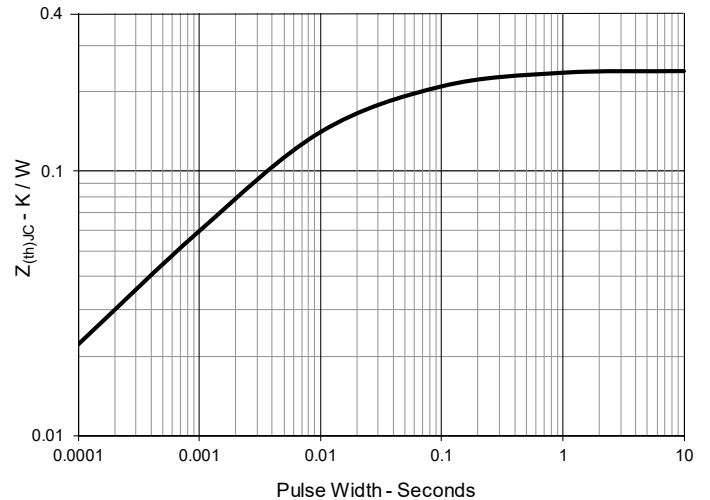
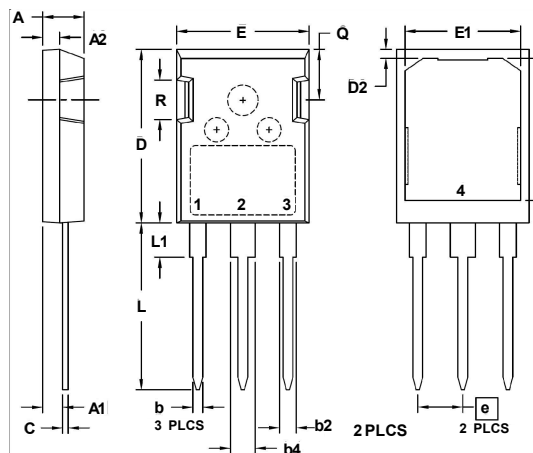
Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature


Fig. 22. Diode Forward Characteristics

Fig. 23. Reverse Recovery Charge vs. $-di_F/dt$

Fig. 24. Reverse Recovery Current vs. $-di_F/dt$

Fig. 25. Reverse Recovery Time vs. $-di_F/dt$

Fig. 26. Dynamic Parameters Q_{RR} , I_{RR} vs. Junction Temperature

Fig. 27. Maximum Transient Thermal Impedance (Diode)


PLUS247™ Outline


1 = Gate
2,4 = Collector
3 = Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.520	.560	13.08	14.22
e	.215 BSC		5.45 BSC	
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83

